

Two-dimensional materials and applications

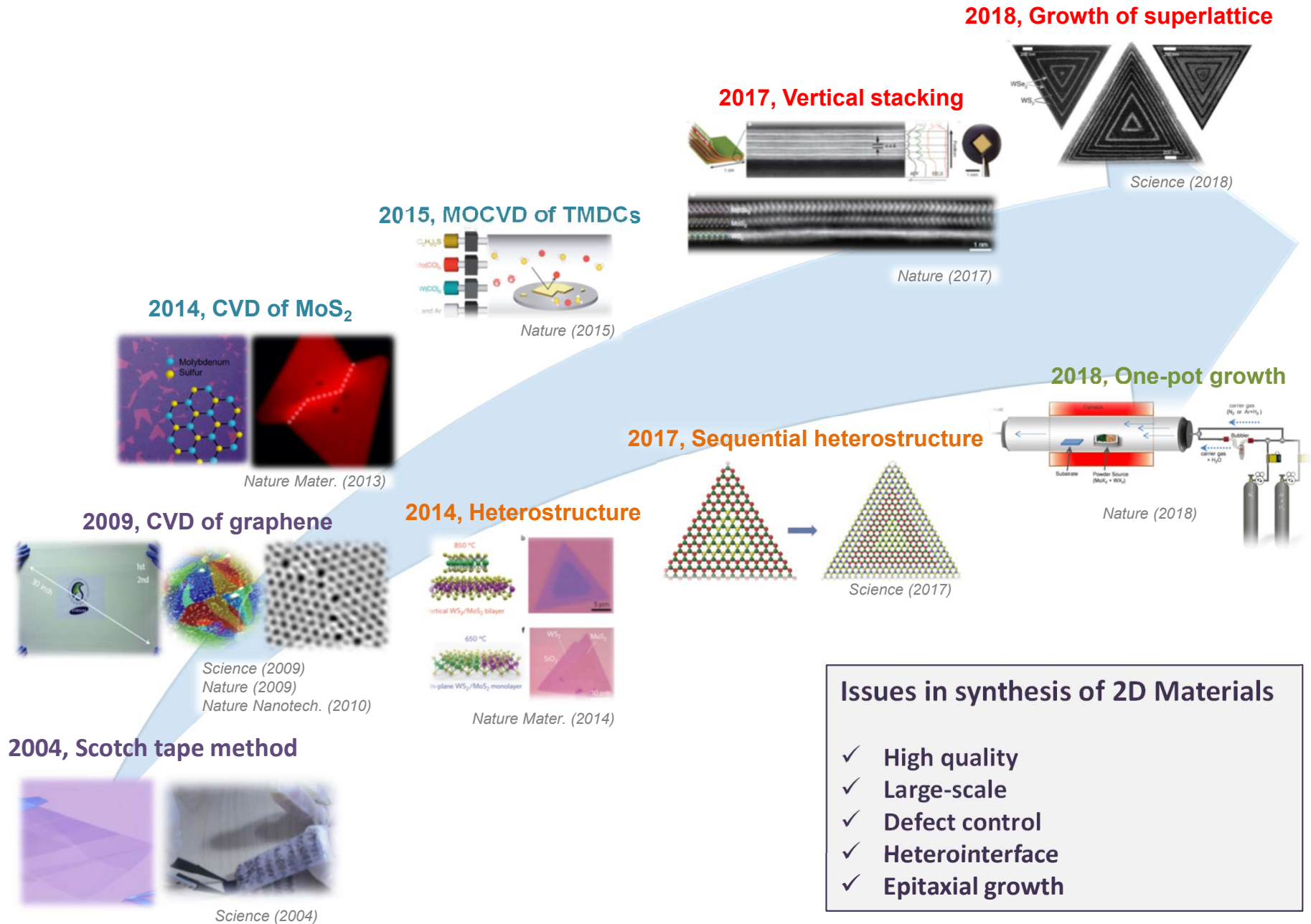
5. Production of 2D Materials

Part 2



서울대학교
SEOUL NATIONAL UNIVERSITY

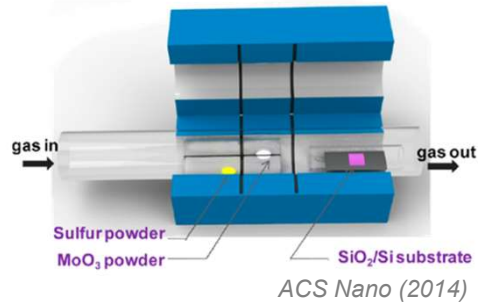
History of Synthesis in 2D Materials



- Issues in synthesis of 2D Materials**
- ✓ High quality
 - ✓ Large-scale
 - ✓ Defect control
 - ✓ Heterointerface
 - ✓ Epitaxial growth

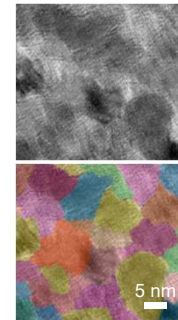
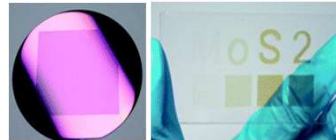
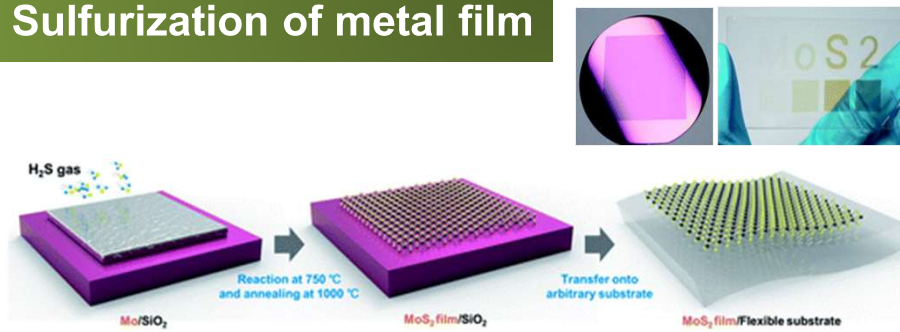
Source Supply for 2D Material Growth

1. Evaporation of powder



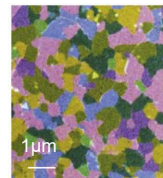
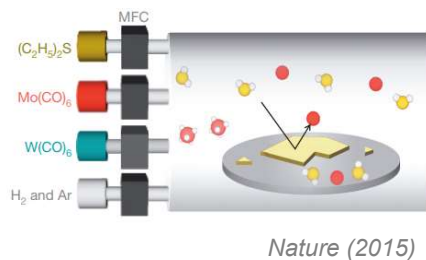
- ✓ High quality crystal
- ✓ Easy process
- ✓ **Not continuous**
- ✓ **Less practical**

2. Sulfurization of metal film



- ✓ Large-scale growth
- ✓ Continuous film
- ✓ Thickness-controllable
- ✓ **Nano-size grains**
- ✓ **Non-stitched grains**

3. Metal-organic source

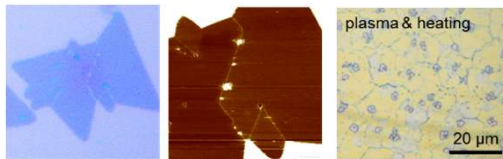
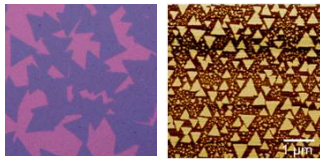
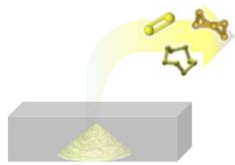
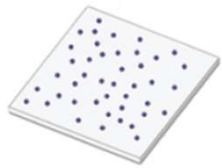


- ✓ Larger grain size
- ✓ Continuous film
- ✓ **Long process time (>10h)**
- ✓ **Grain boundaries**

Main Stages for 2D Material Growth

Nucleation

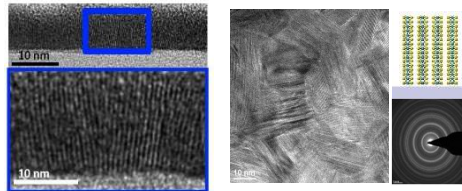
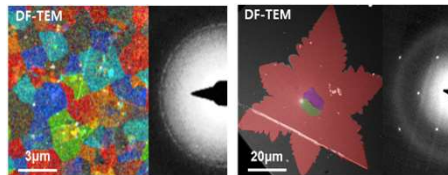
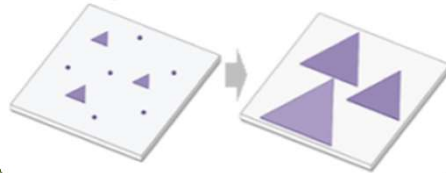
Nucleation sites
Seed
Flatness



Nature Mater. (2013)

Growth

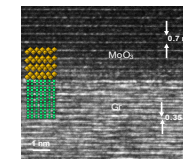
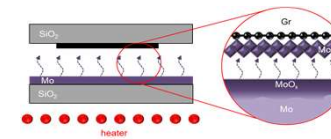
Coalescence
Abnormal growth
Stitching



Science (2013)
ACS Appl. Mater. Inter. (2018)

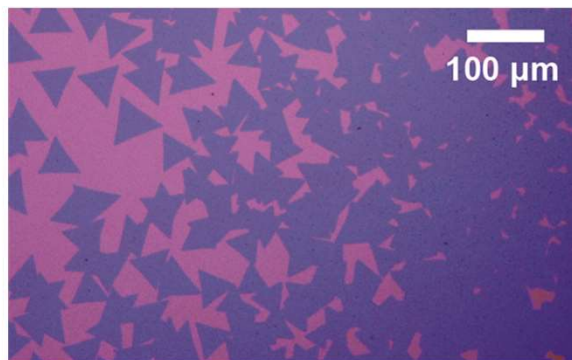
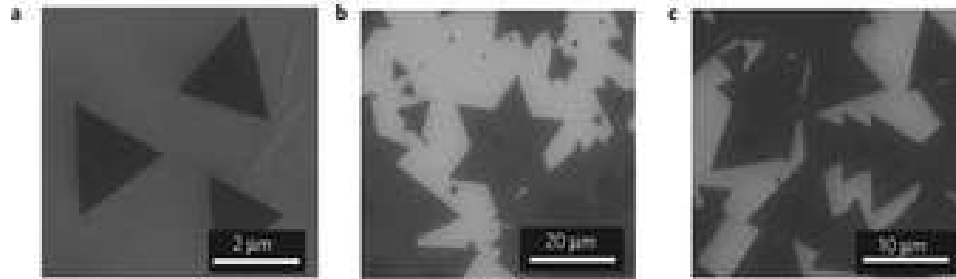
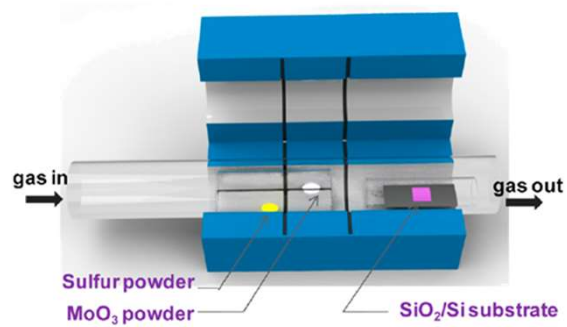
Complete film

Boundary
Epitaxy
Defects

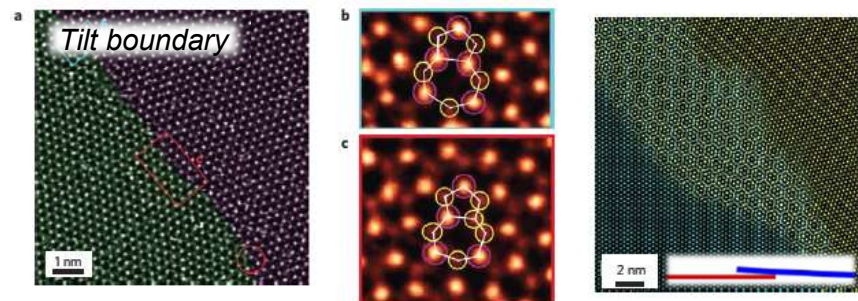
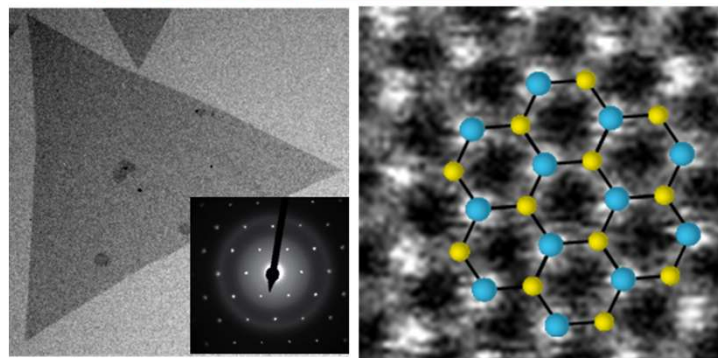
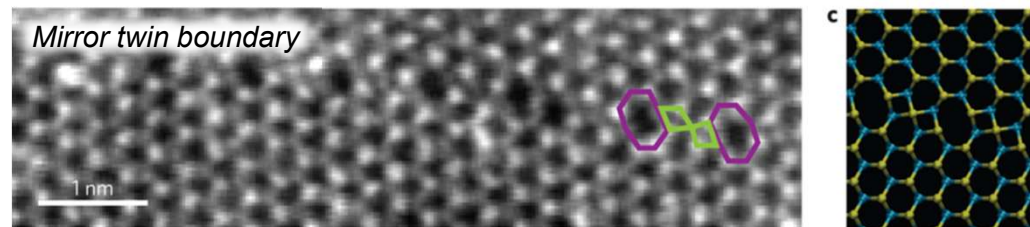


Nature Mater. (2013)
2D Materials (2018)

Chemical Vapor Deposition of MoS₂

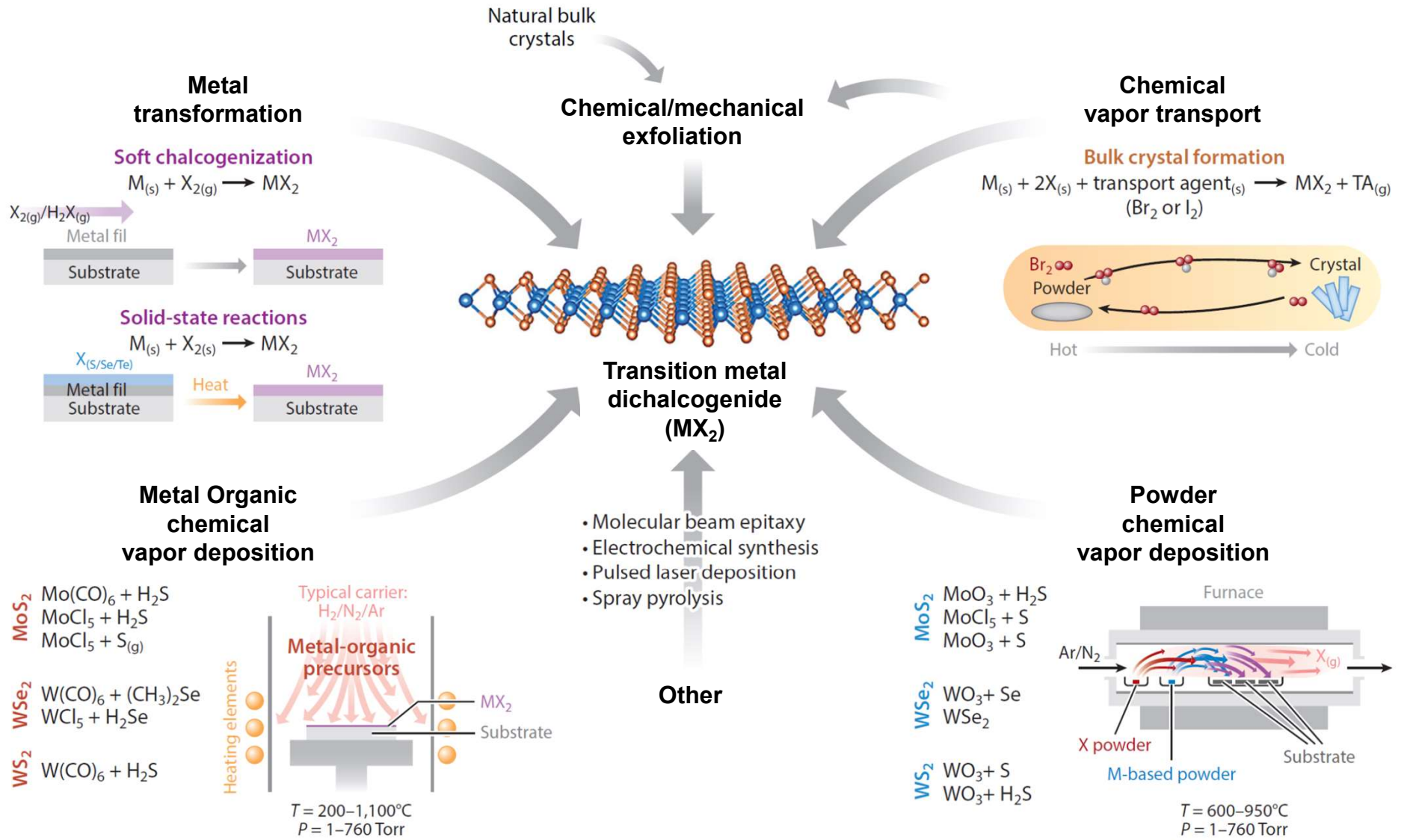


Grain boundaries in CVD-grown MoS₂



Mirror twin boundary: 8-4-4 defects (n-doped Mo-rich)
Tilt boundary: 5-7 defects (p-doped S-rich)

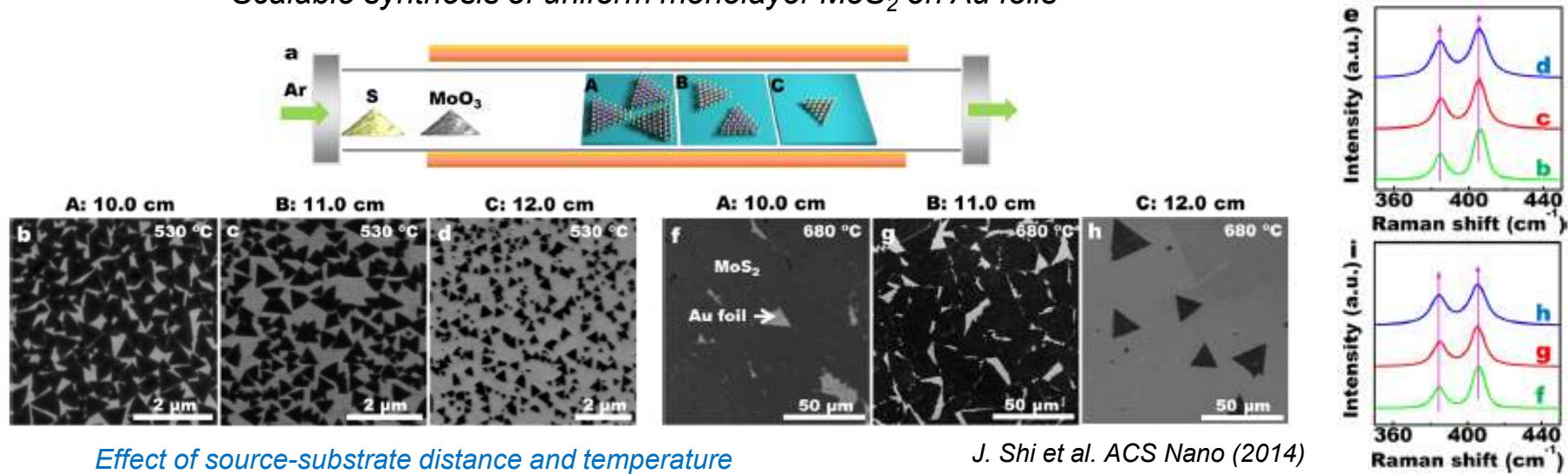
Map of 2D Material Synthesis



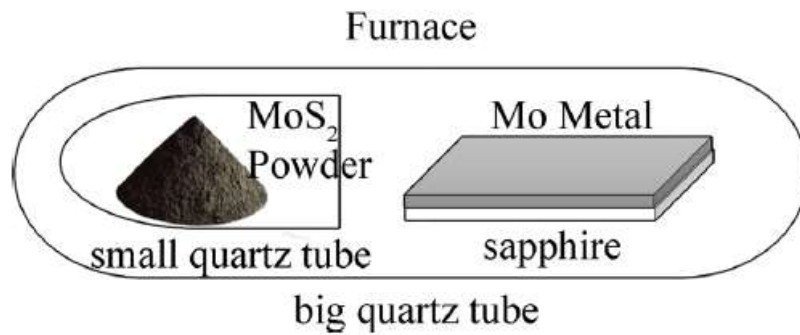
S. Das, J.A. Robinson, M. Terrones, et al.
 Annual Review of Materials Research (2015)

Growth Method I

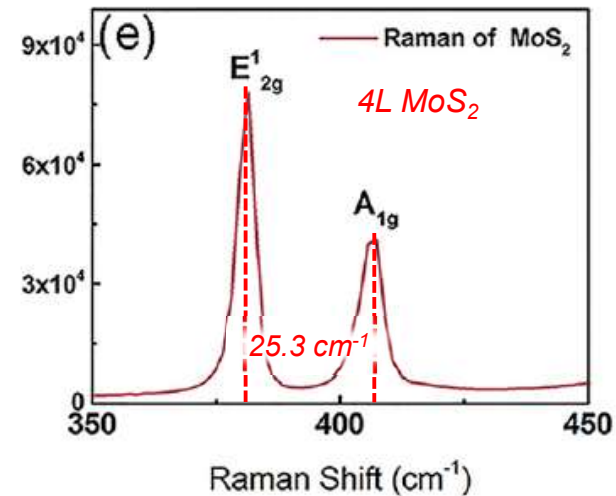
Scalable synthesis of uniform monolayer MoS₂ on Au foils



Multilayer MoS₂ on sapphire

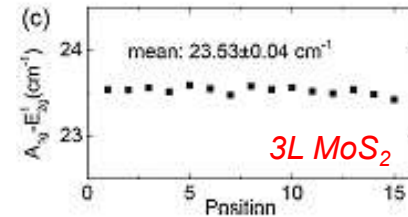
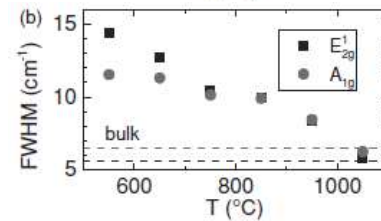
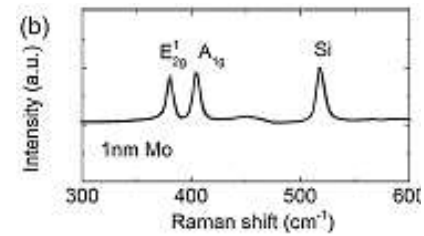
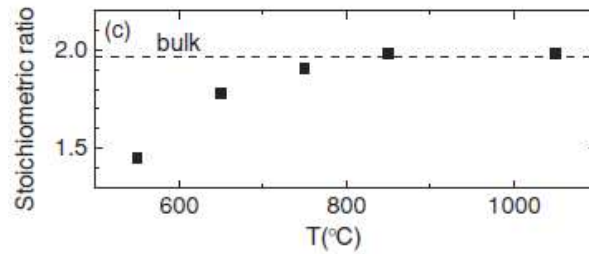


L. Ma et al. Appl. Phys. Lett. (2014)



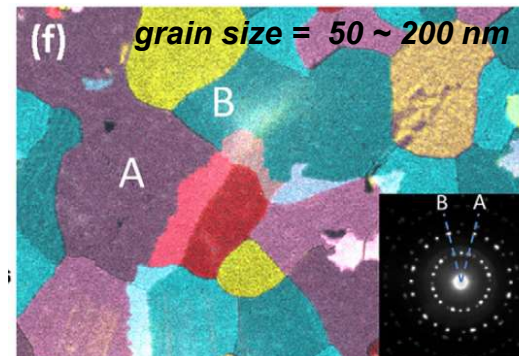
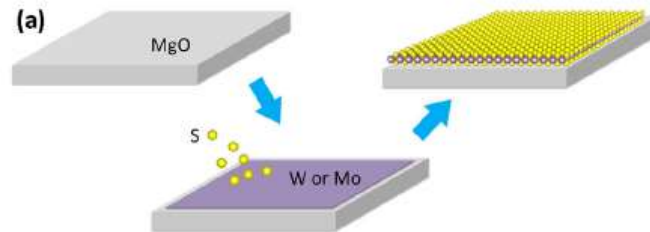
Growth Method II

Sulfurization of Mo thin film



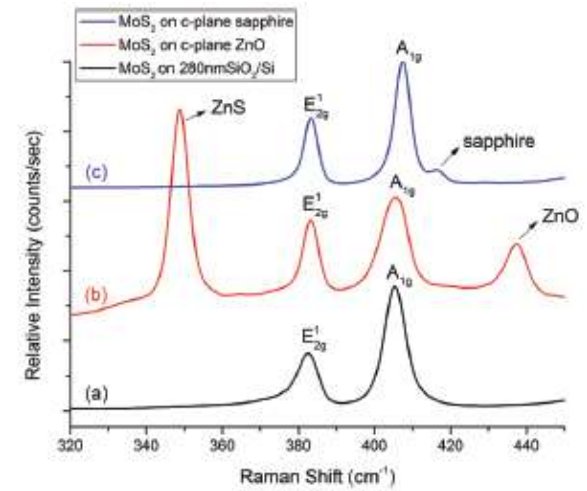
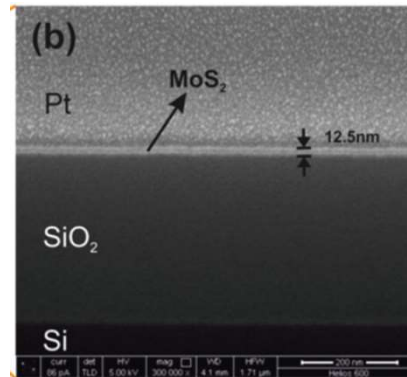
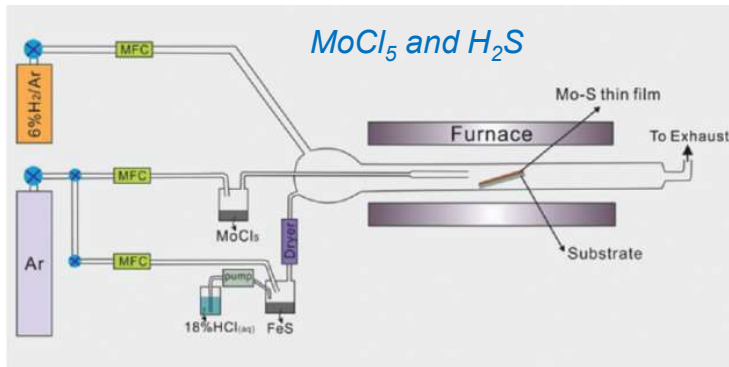
Higher growth temperature is better.

A. Tarasov et al. Adv. Funct. Mater. (2014)



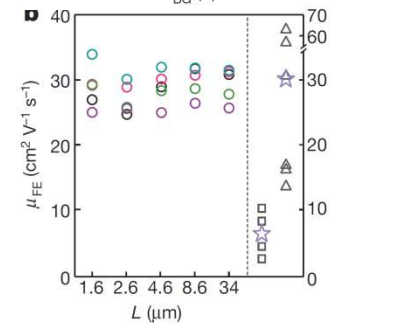
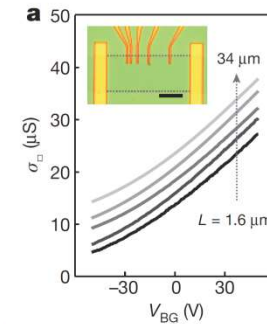
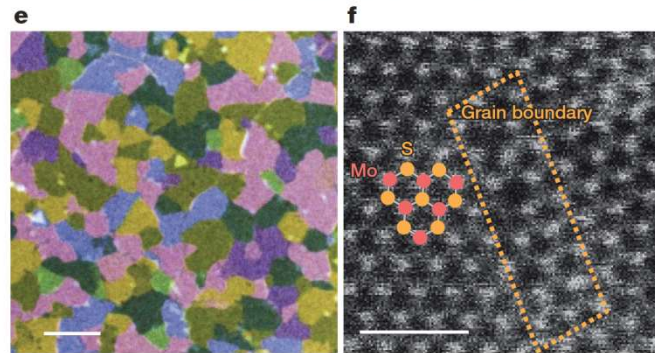
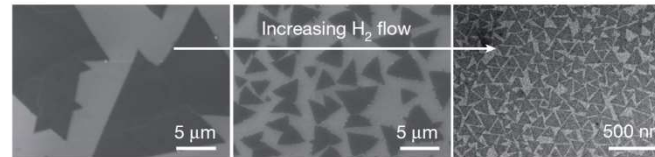
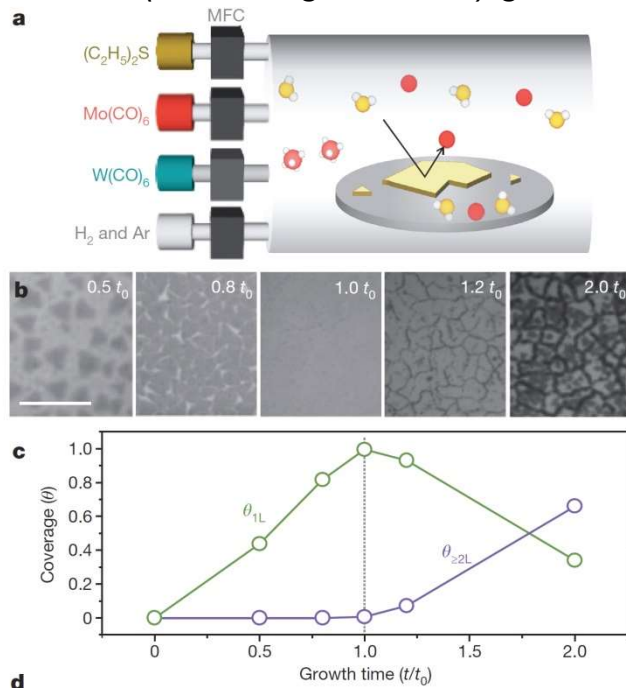
C. M. Orofeo et al. Appl. Phys. Lett. (2014)

Growth Method III



C. C. Huang et al. *Nanoscale* (2014)

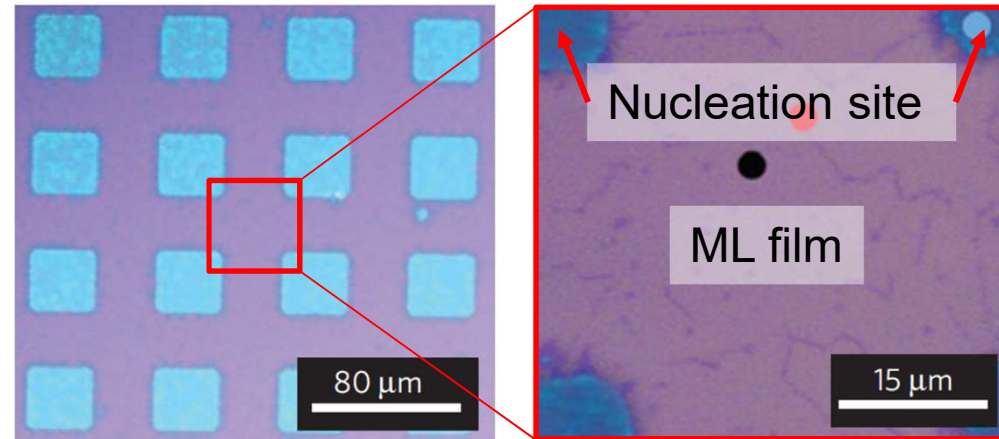
MOCVD (Metal-Organic CVD) growth



K. Kang et al. *Nature* (2015)

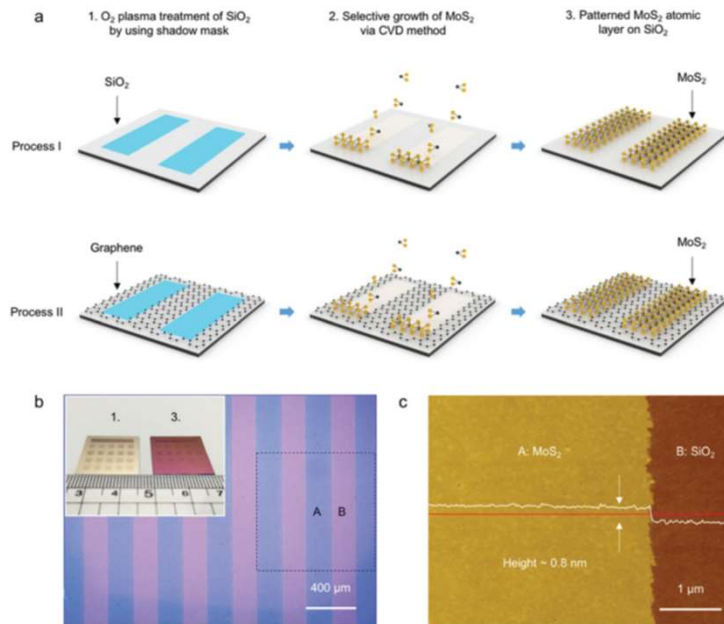
Nucleation and Patterned Growth

Pre-patterned nucleation control (SiO_2 pillars)



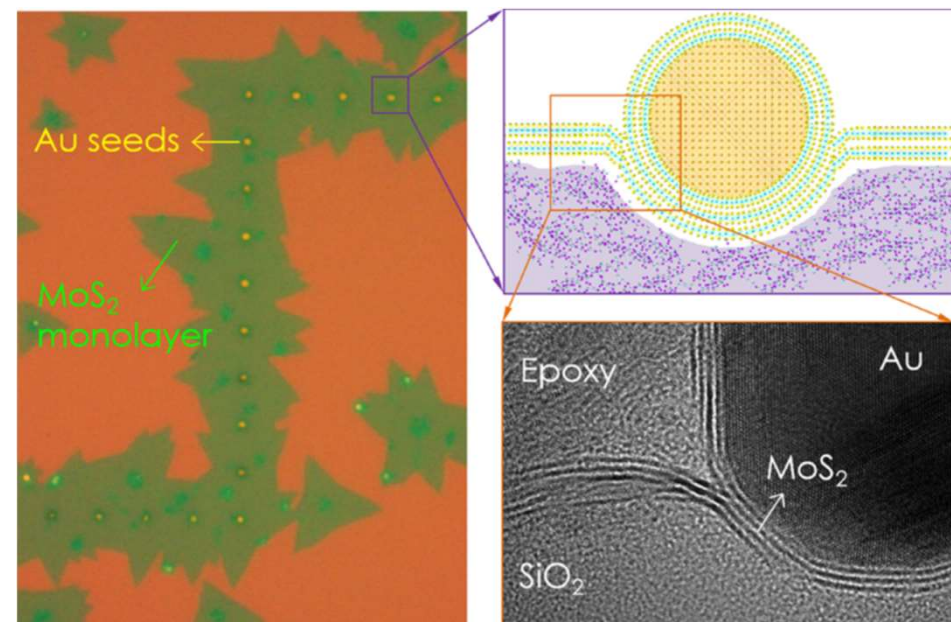
Nazmaei et al. *Nat. Mater.* (2013)

Plasma patterned nucleation control



Chen et al. *Nanoscale* (2016)

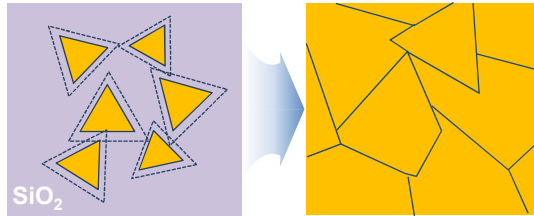
Au patterned nucleation control



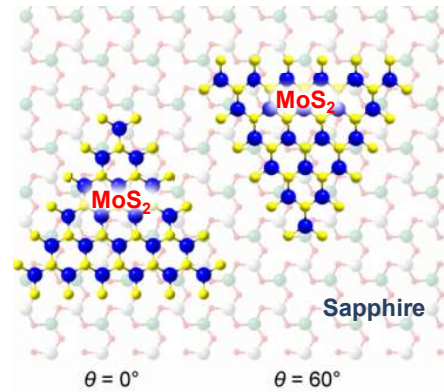
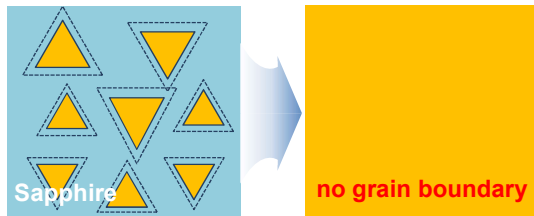
Li et al. *ACS Nano* (2018)

Epitaxial Growth

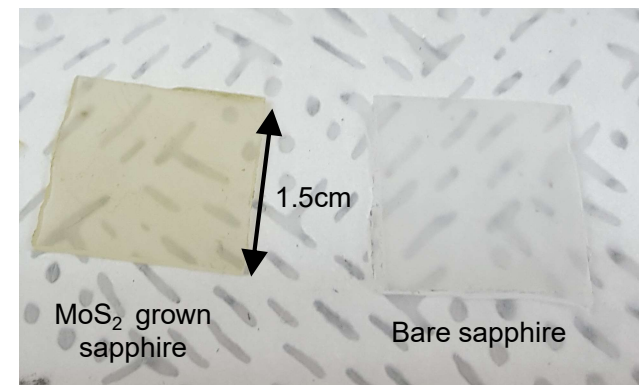
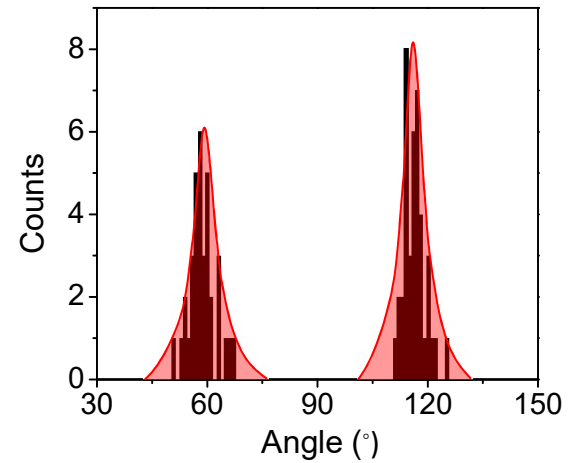
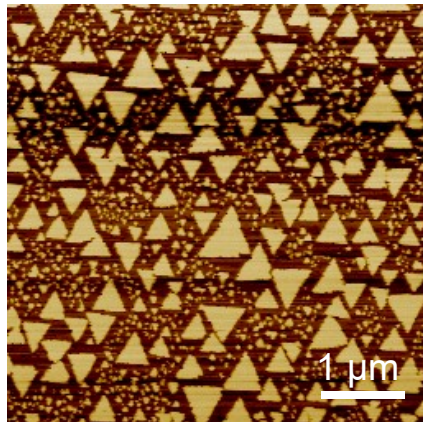
Random growth (polycrystalline)



Epitaxial growth (single crystal)

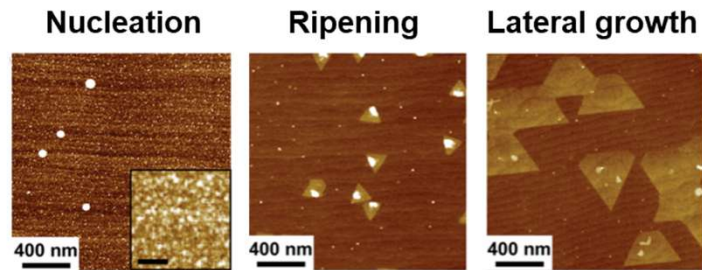
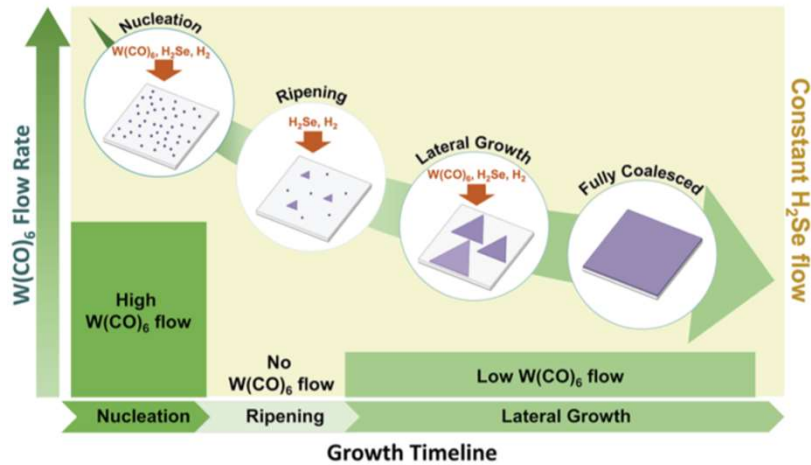


D. Dumcenco, *ACS Nano* (2015)



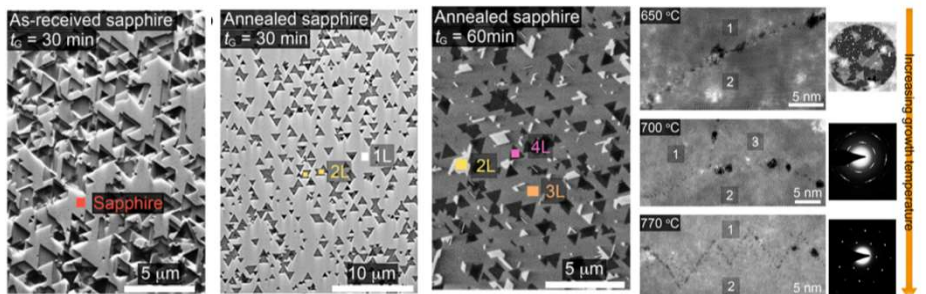
Epitaxial Growth

Three step process of WSe_2 growth on *c*-Sapphire



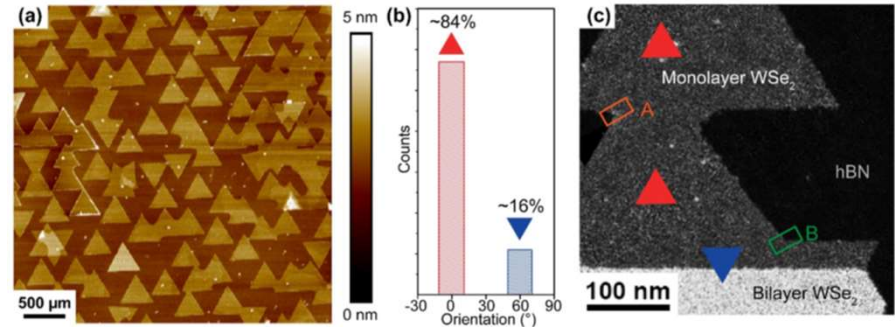
X. Zhang, et al. *Nano Lett.* (2018)

Epitaxial growth of WSe_2 on *c*-sapphire



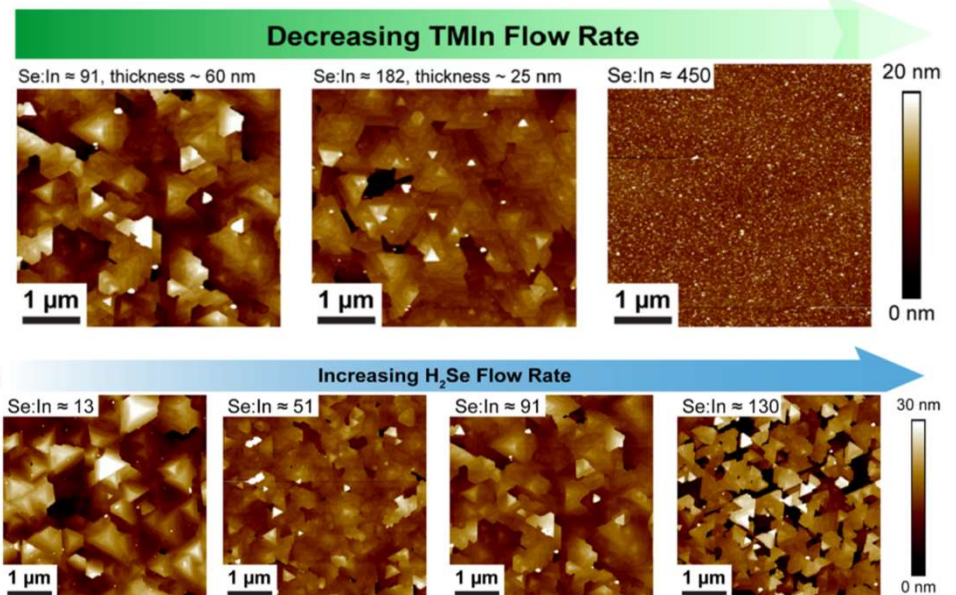
Y. Lin, et al. *ACS Nano.* (2018)

Epitaxial growth of WSe_2 on *h*-BN



X. Zhang, et al. *ACS Nano.* (2019)

Epitaxial growth of In_2Se_3 on *c*-sapphire

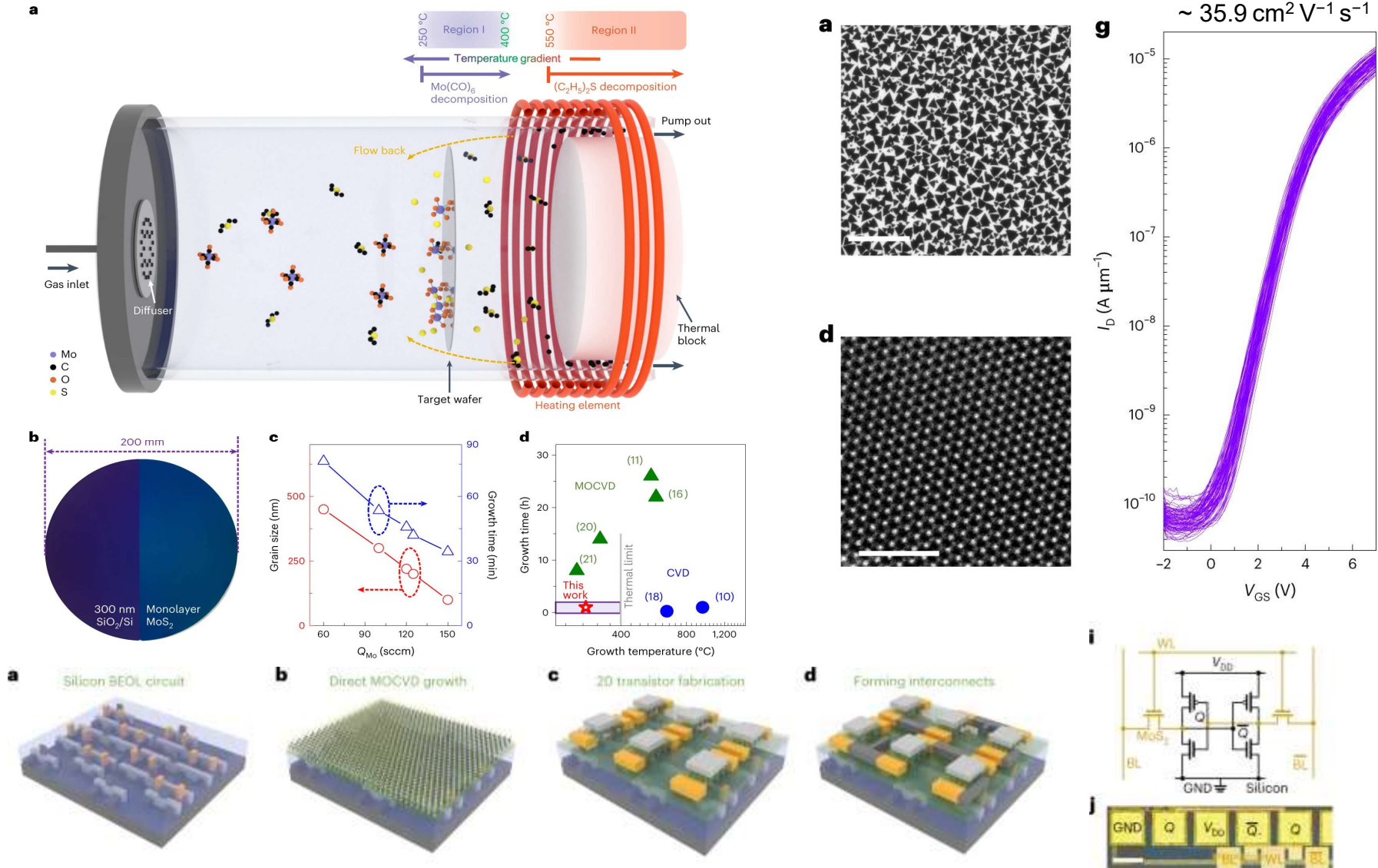


Zhang et al. *J. Cryst. Growth* (2020)

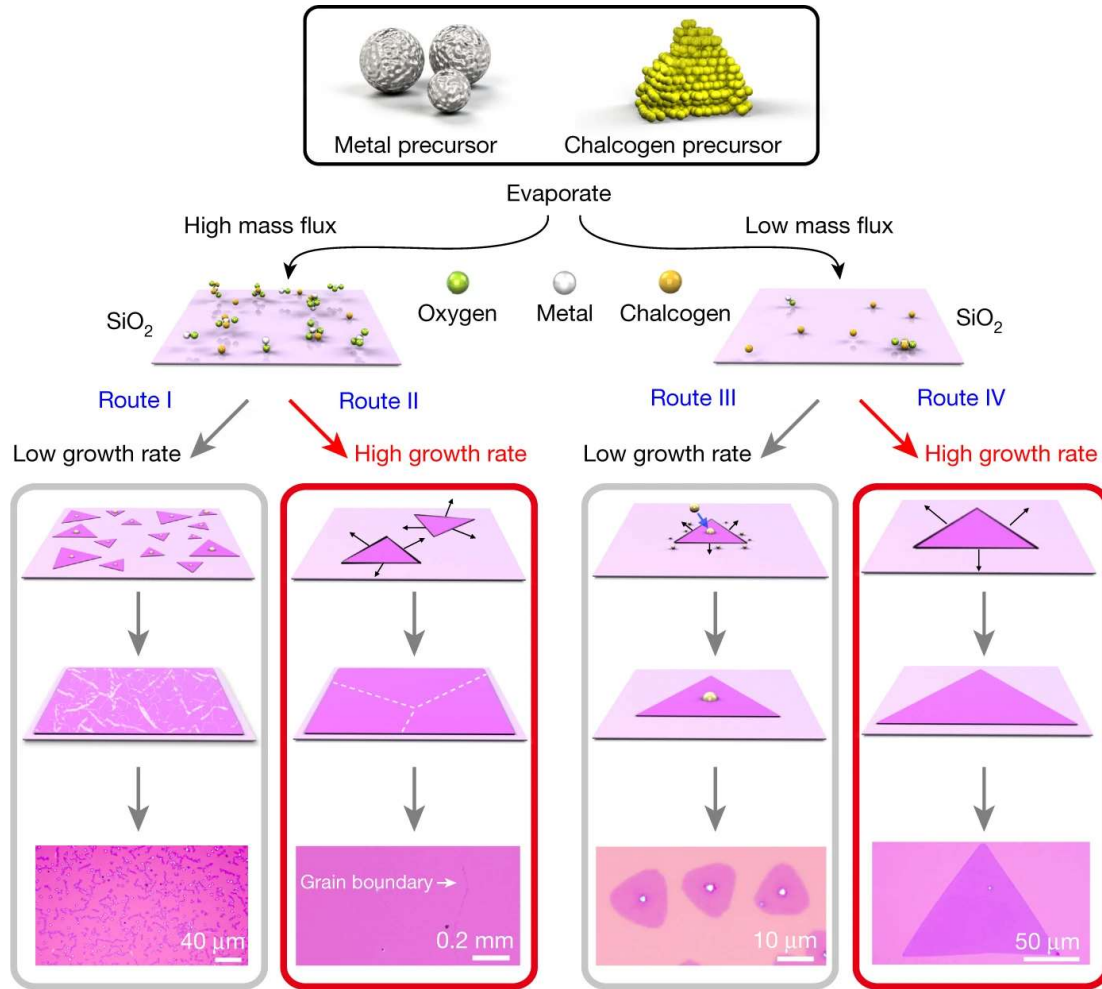
Low Temperature Growth of MoS₂

Safe temperature for the silicon process (400°C)

Decomposition temperatures of Mo(CO)₆ (~250°C) and (C₂H₅)₂S (550°C)

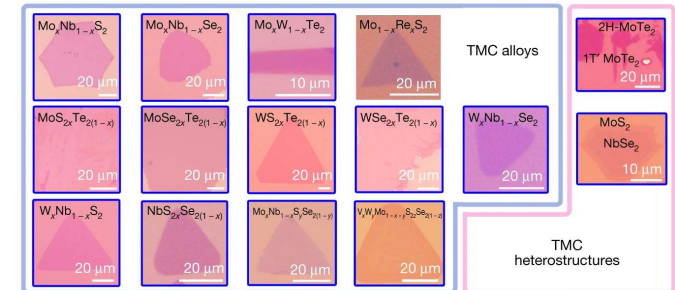
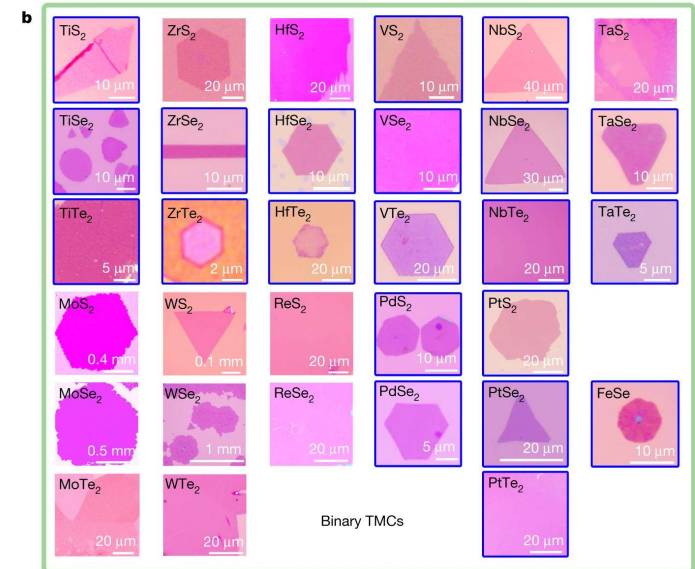


Promoter-assisted MOCVD



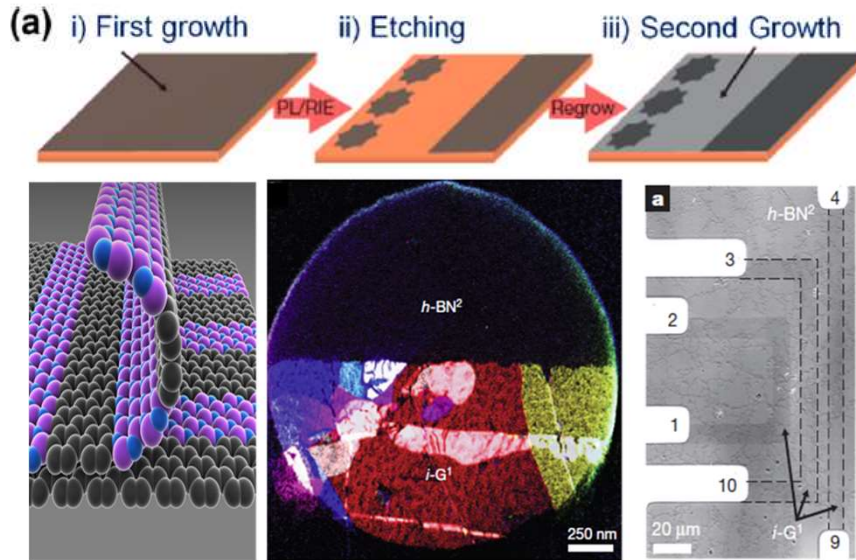
a

IIIB	IVB	VB	VIB	VIIIB	VIII		IB	VA	VIA	VIIA	
Sc 21	Ti 22	V 23	Cr 24	Mn 25	Fe 26	Co 27	Ni 28	Cu 29	P 15	S 16	Cl 17
Y 39	Zr 40	Nb 41	Mo 42	Tc 43	Ru 44	Rh 45	Pd 46	Ag 47	As 33	Se 34	Br 35
La 57	Hf 72	Ta 73	W 74	Re 75	Os 76	Ir 77	Pt 78	Au 79	Sb 51	Te 52	I 53

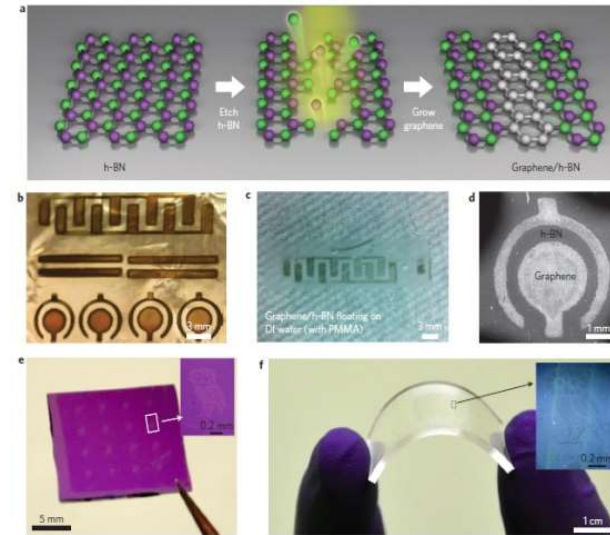


Growth of Heterostructures

Growth of graphene-hBN heterostructure

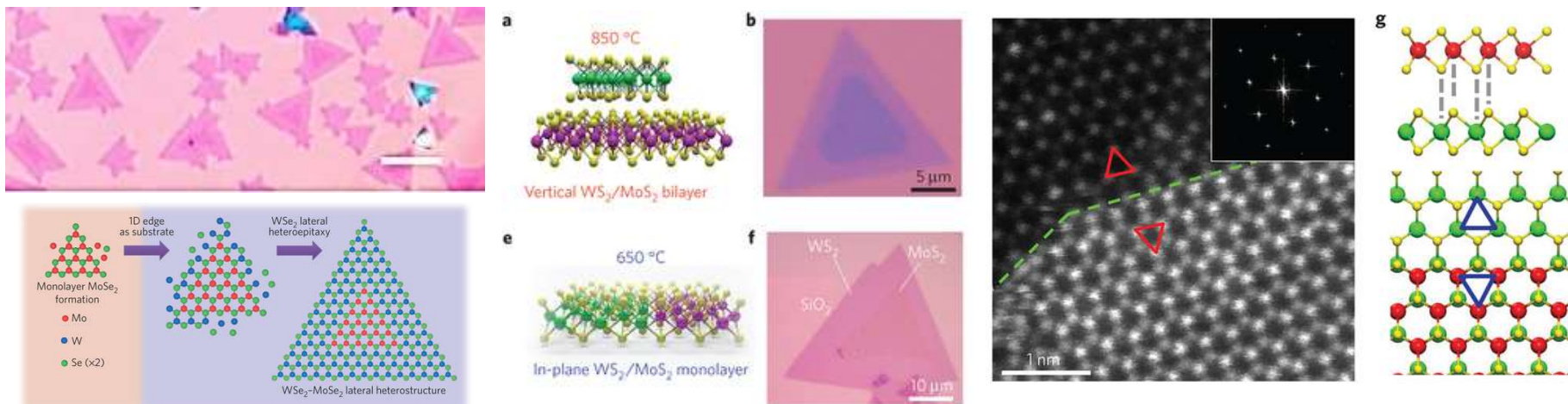


M. P. Levendorf et al. Nature (2012)



Z. Liu et al. Nat. Nanotech. (2013)

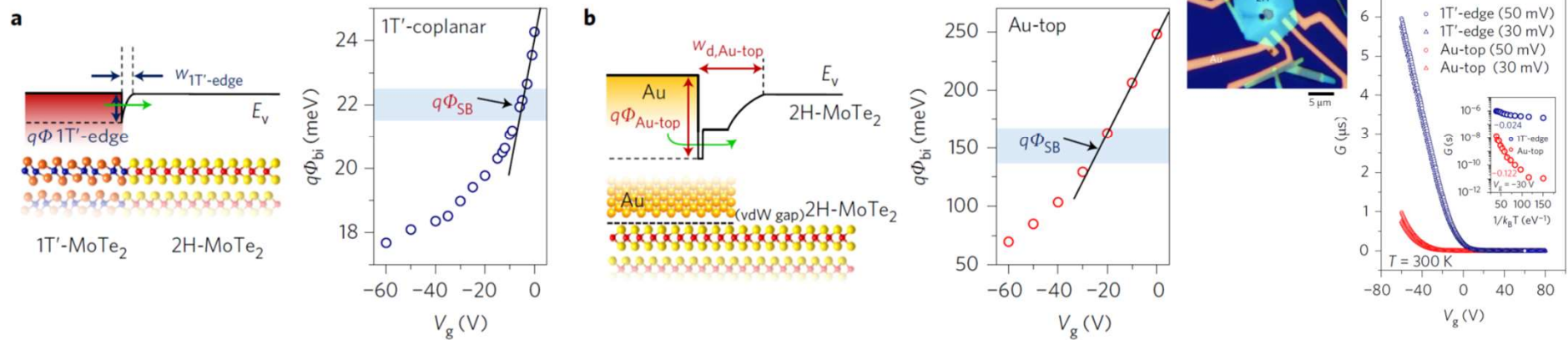
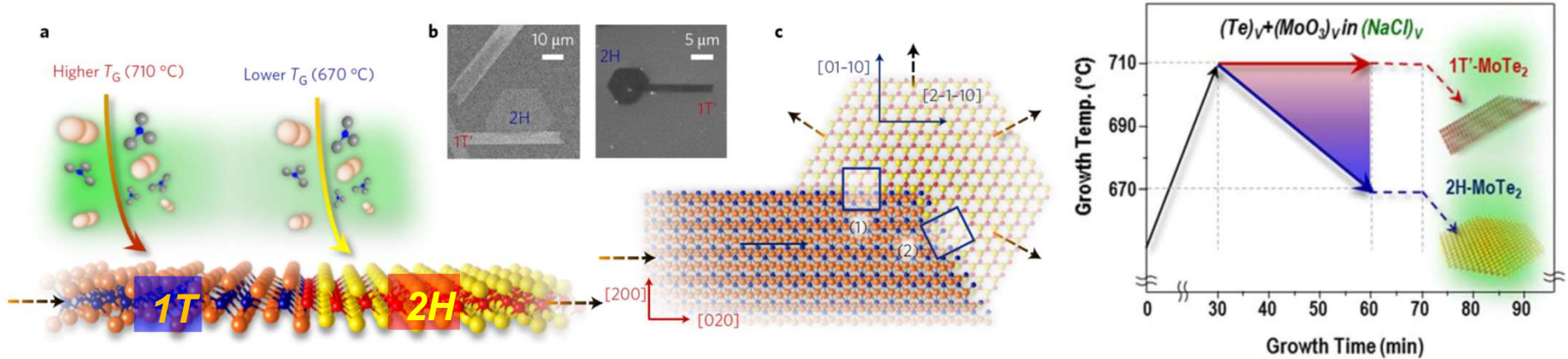
Growth of semiconductor heterostructure



C. Huang et al. Nature Mater. (2014) & Y. Gong et al. Nature Mater. (2014) & G. S. Duesberg et al. Nature Mater. (2014)

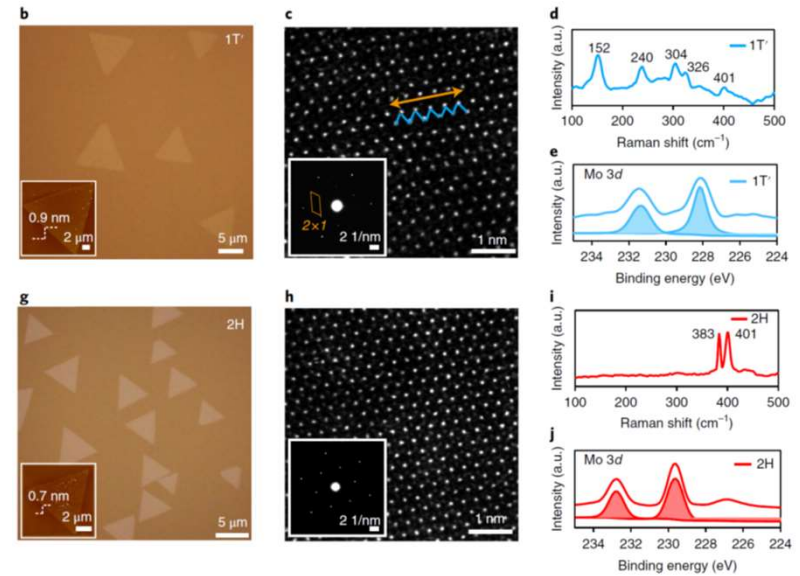
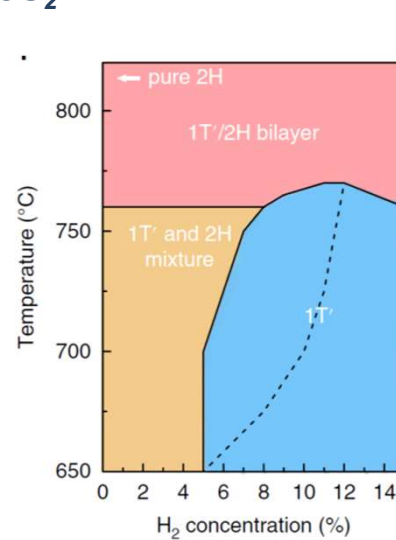
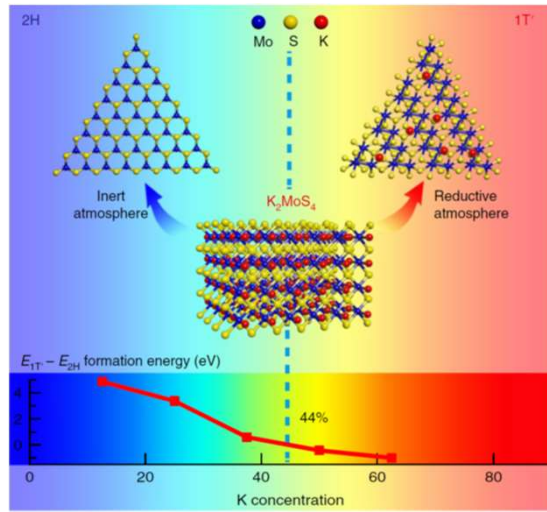
Growth of Heterostructures

Sequential growth of coplanar heteroepitaxy (1T'/2H MoTe₂)

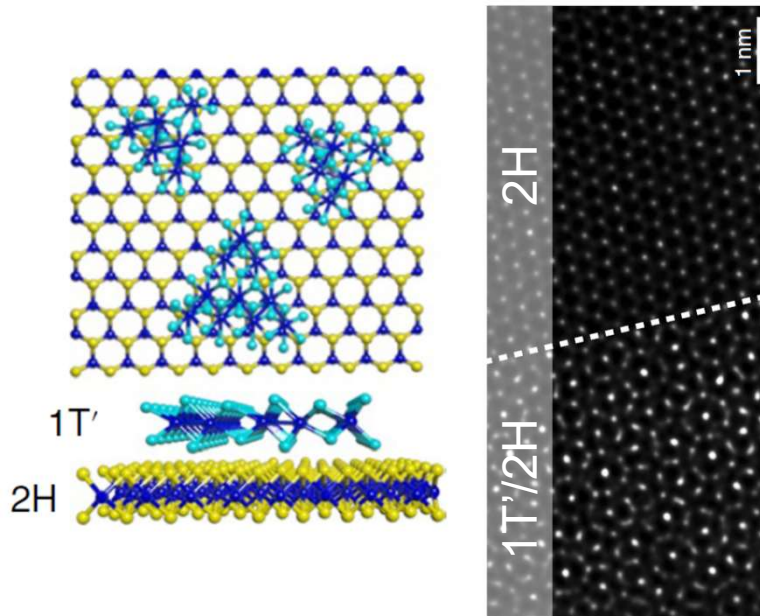


Growth of Heterostructures

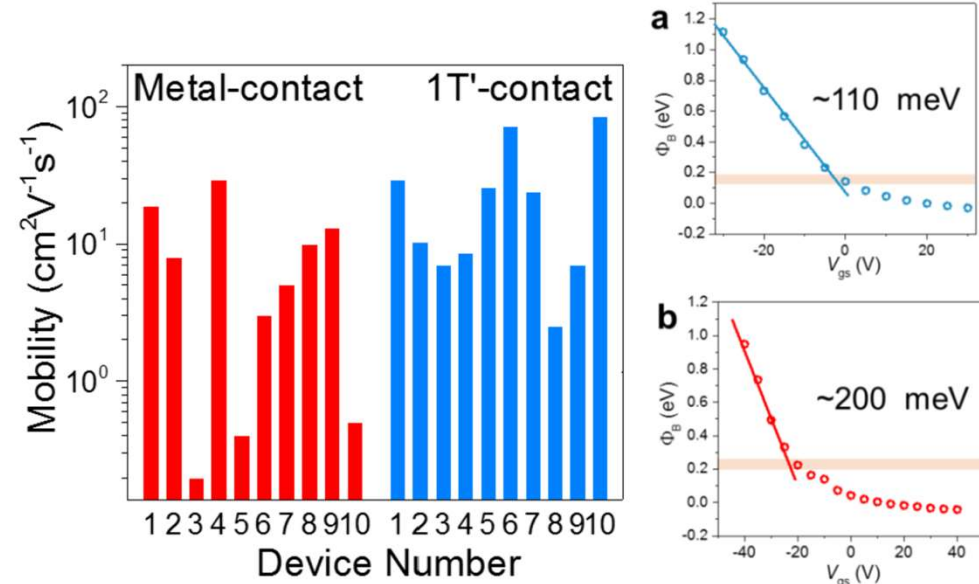
Phase-selective synthesis of MoS₂



Heterophase of 1T'/2H Bilayer



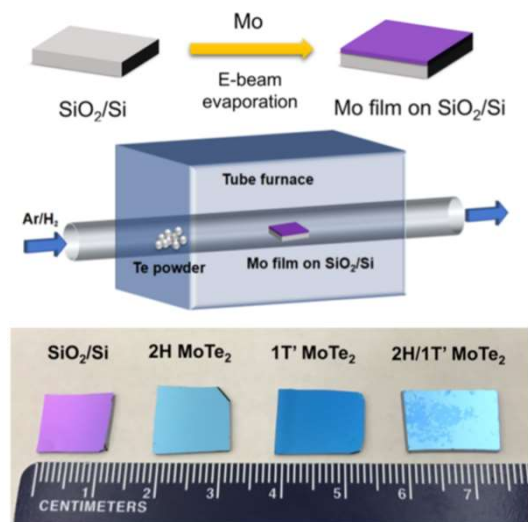
Electrical properties of heterophase contacts



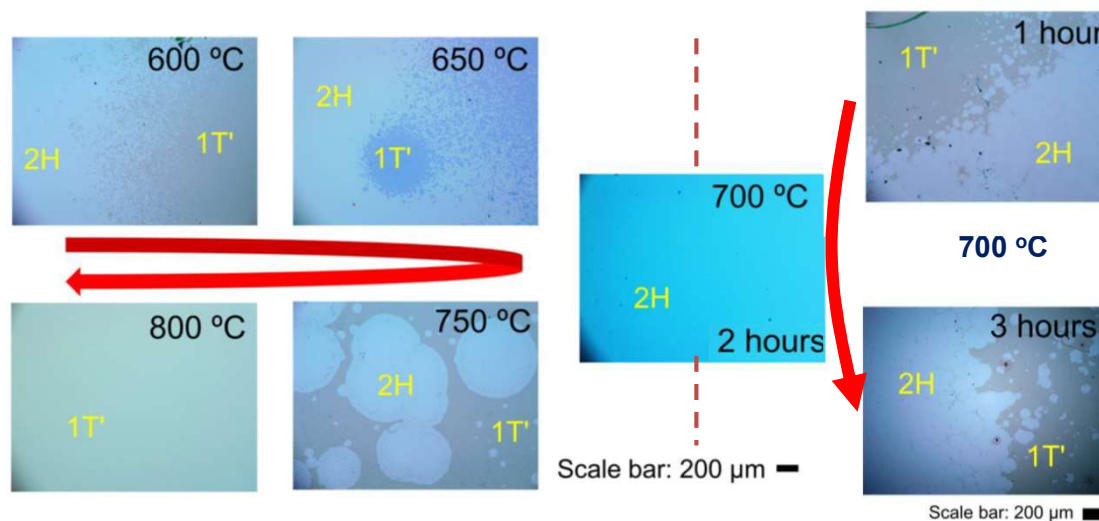
Liu et al. Nat. Mater. (2018)

Growth of Heterostructures

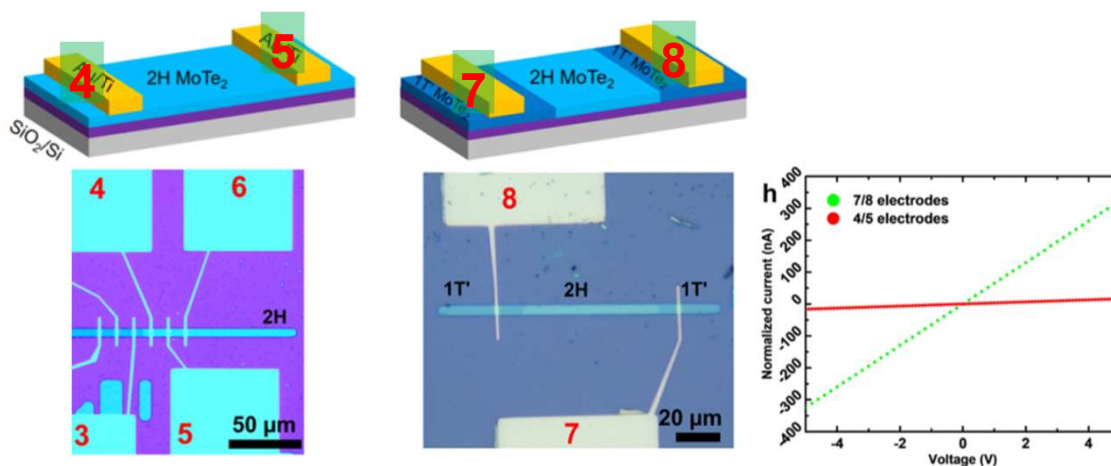
Growth of MoTe_2



Effect of temperature and time on the phase

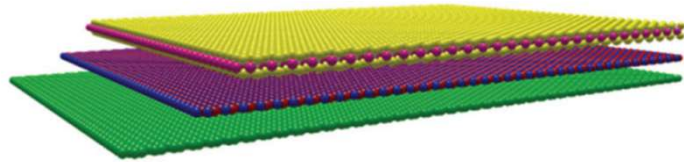


$1\text{T}'$ edge contacts to 2H-MoTe_2

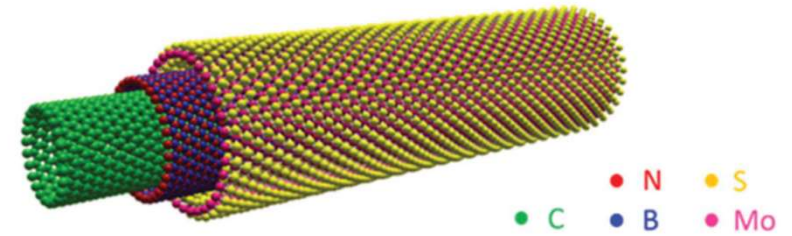


Growth of Heterostructures V

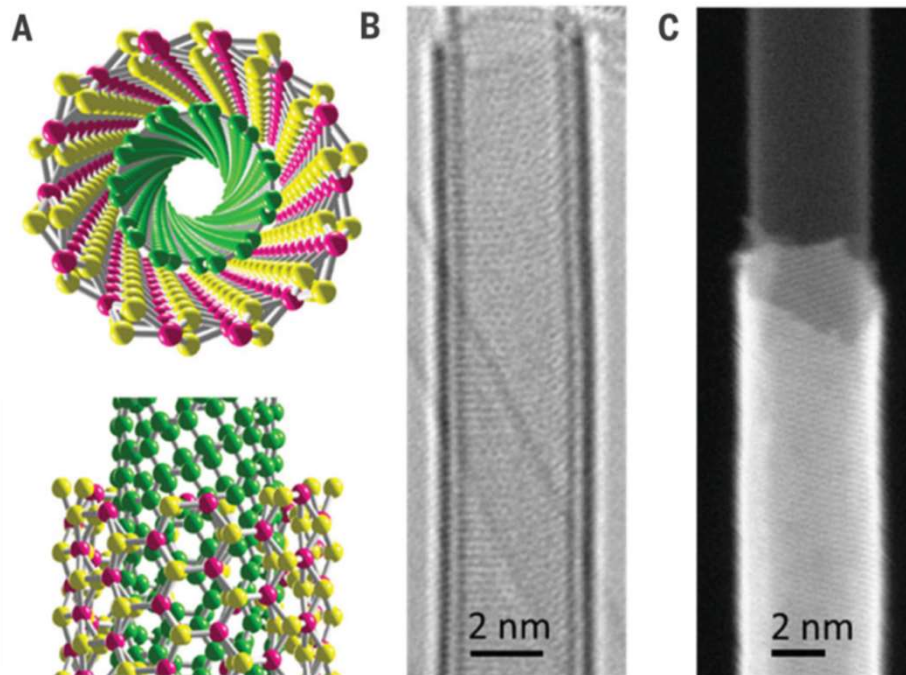
Conventional two-dimensional vdW Heterostructure



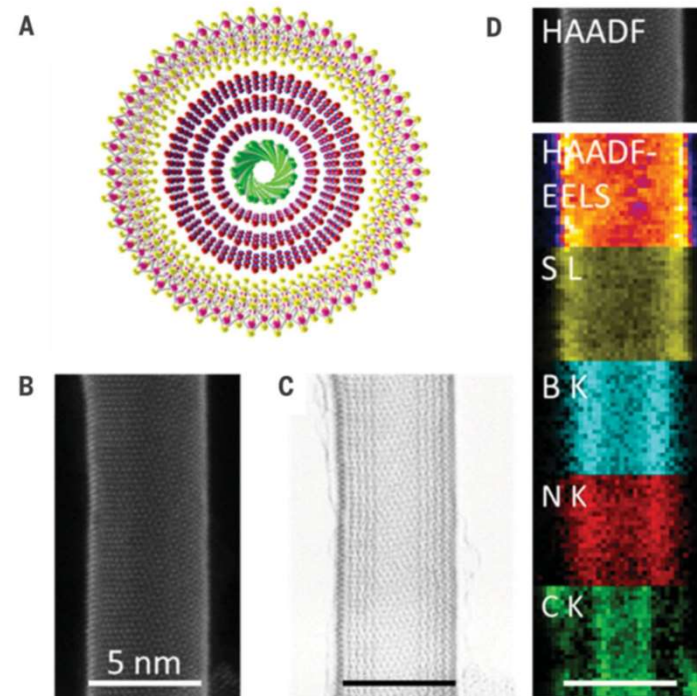
One-dimensional vdW Heterostructure (nanotube)



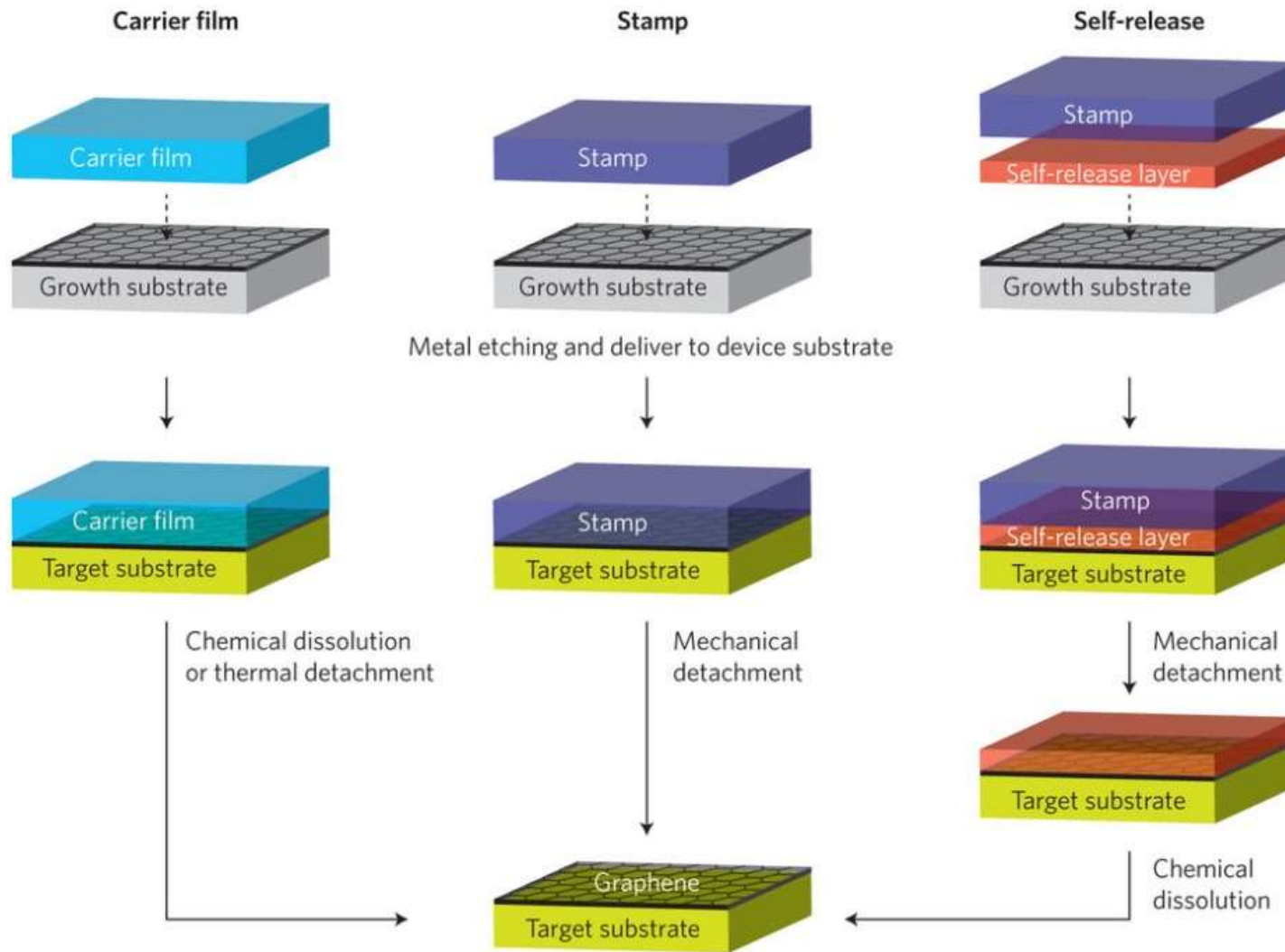
CNT-MoS₂ nanotube heterostructure



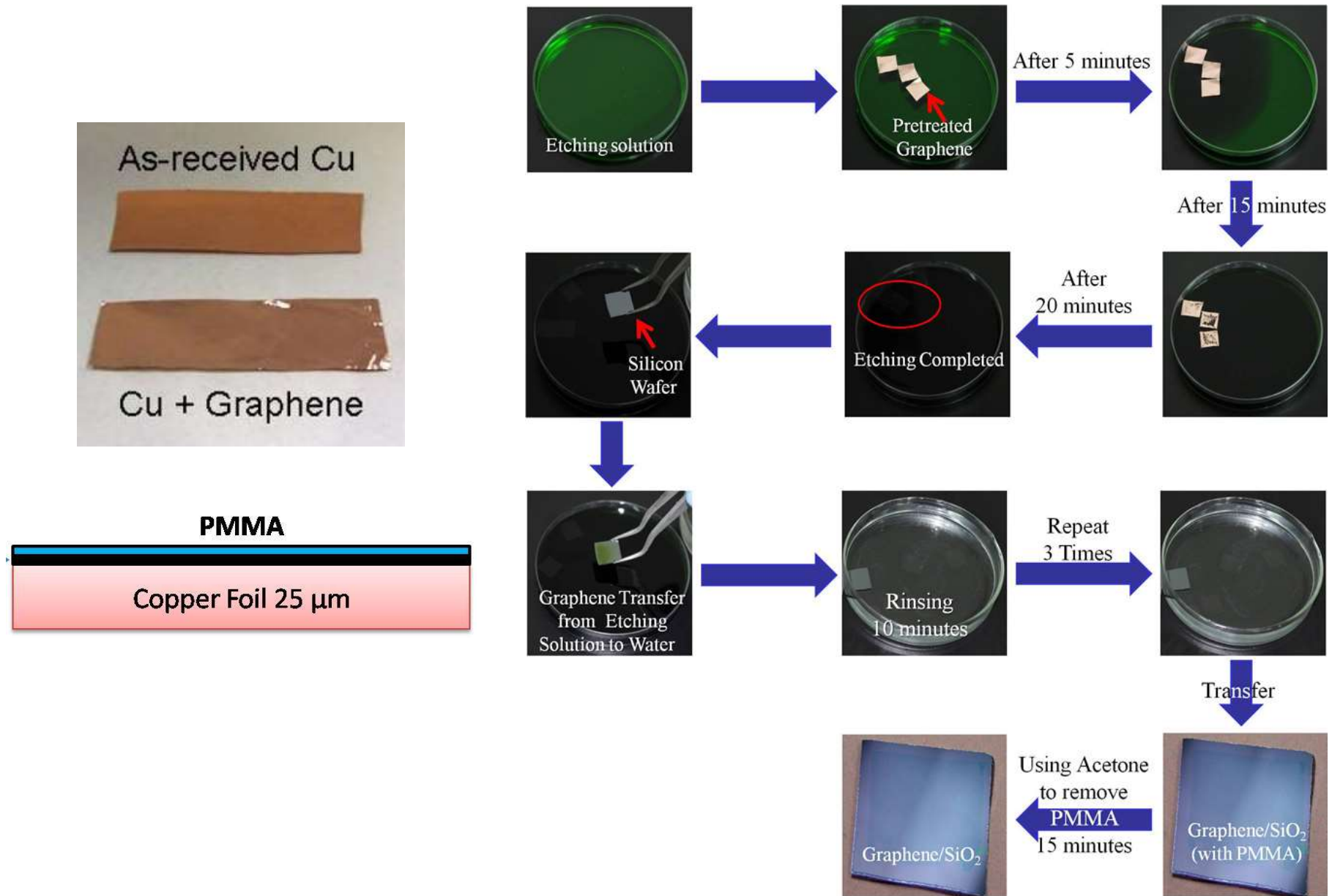
CNT-BNNT-MoS₂ heterostructure



Graphene Transfer Techniques

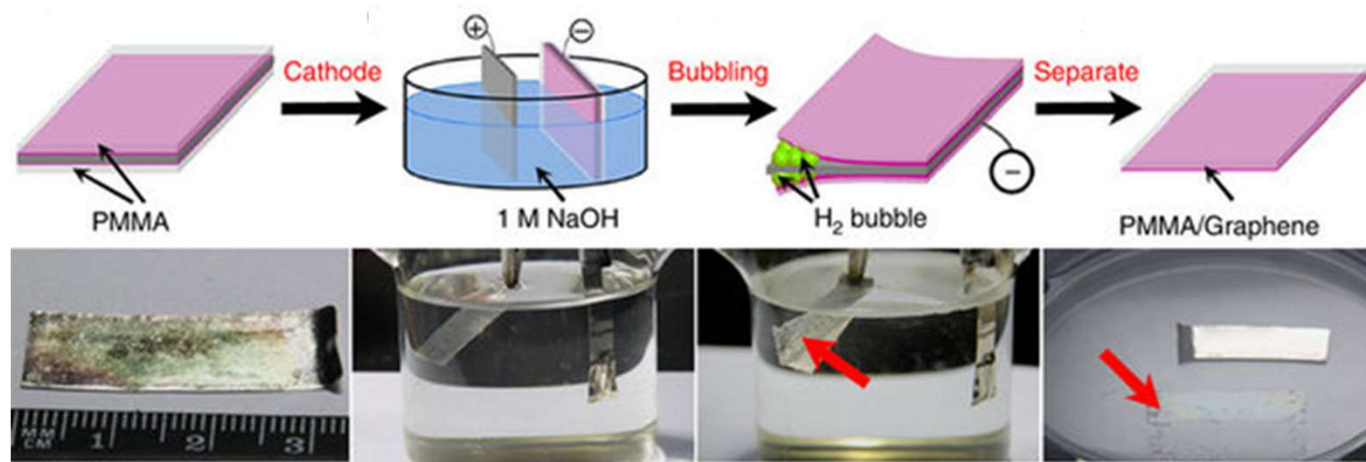


General PMMA Transfer Technique



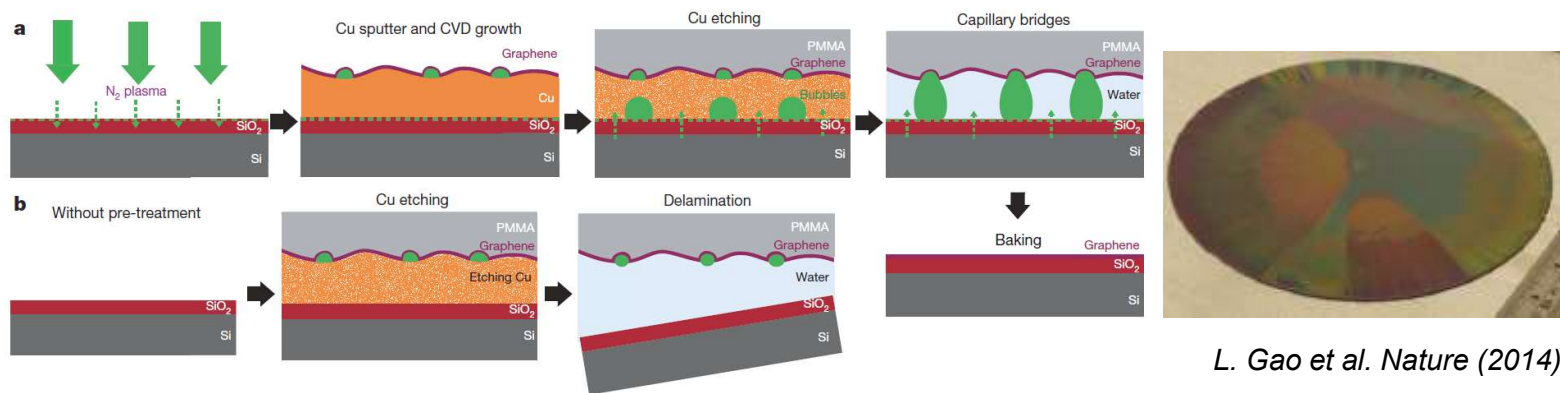
Other Transfer Techniques

Bubble Transfer Technique



L. Gao et al. Nature Commun. (2012) & C. J. Lockhart de la Rosa et al. Appl. Phys. Lett. (2013)

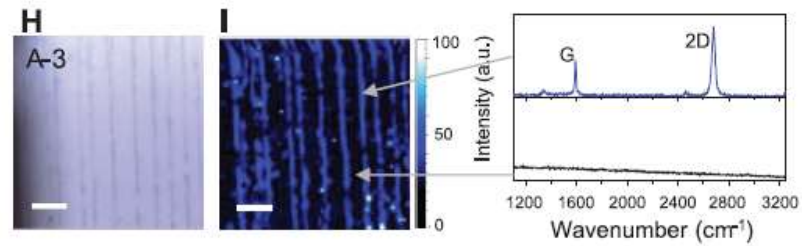
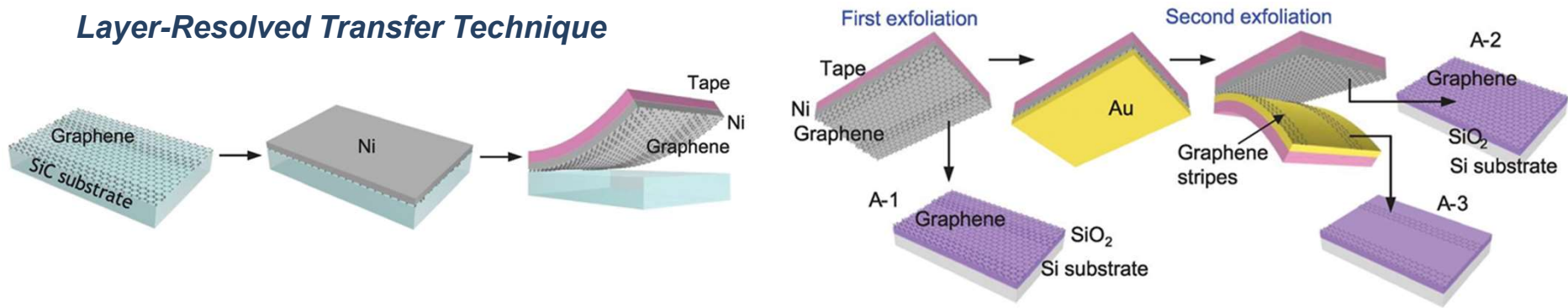
Face-to-Face Transfer Technique



L. Gao et al. Nature (2014)

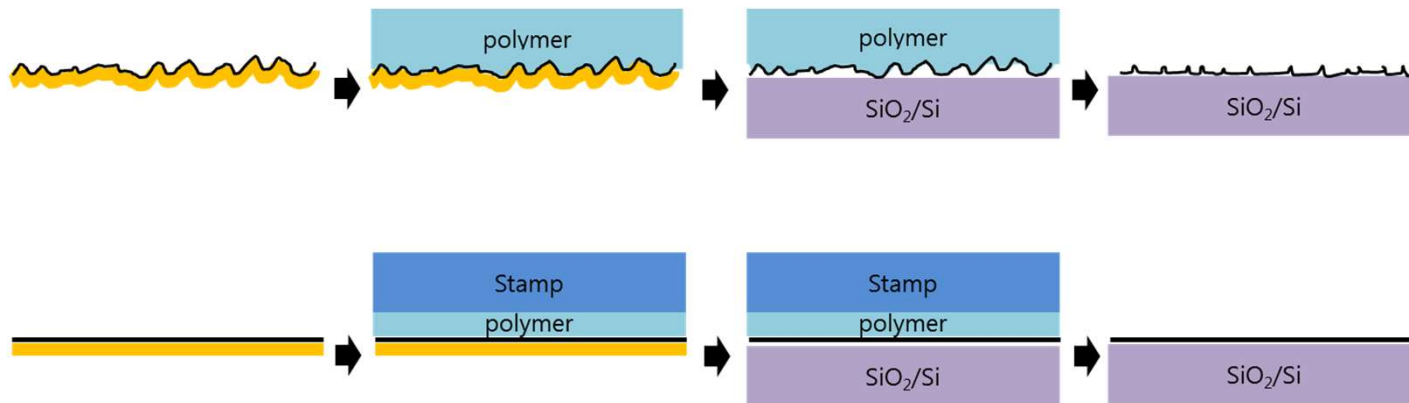
Other Transfer Techniques

Layer-Resolved Transfer Technique



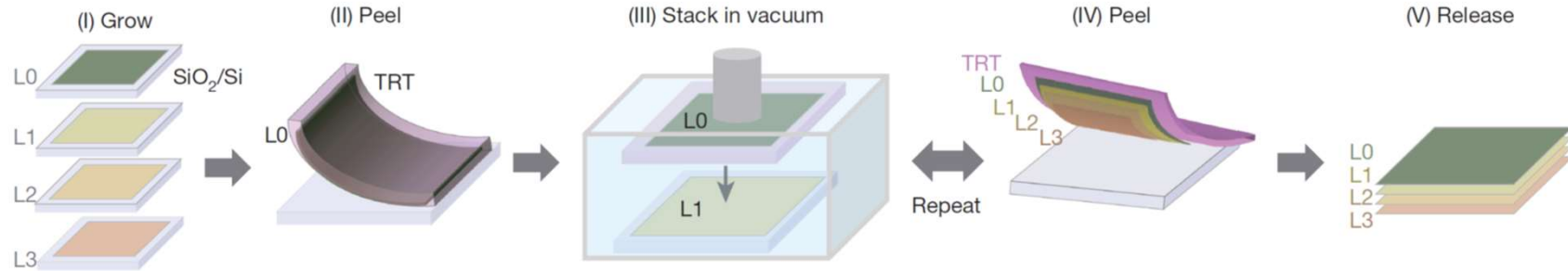
J. Kim et al. Science (2013)

Critical issues in transfer and stacking processes

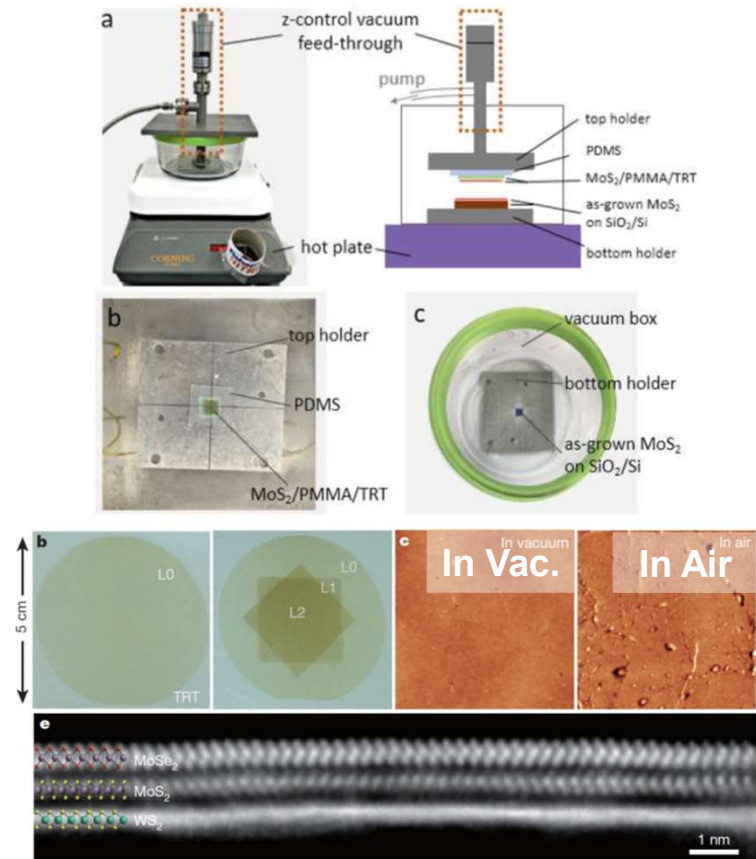
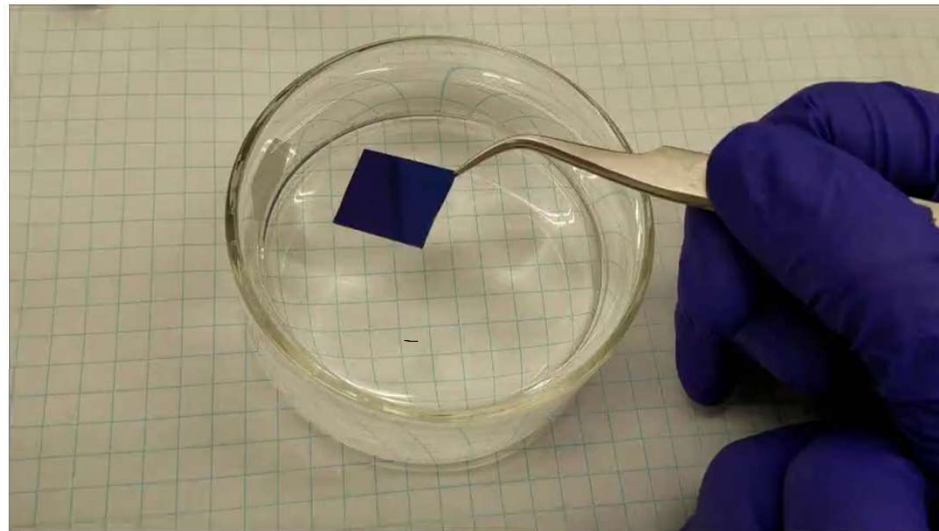


Other Transfer Techniques

Layer-by-layer assembly of TMDs

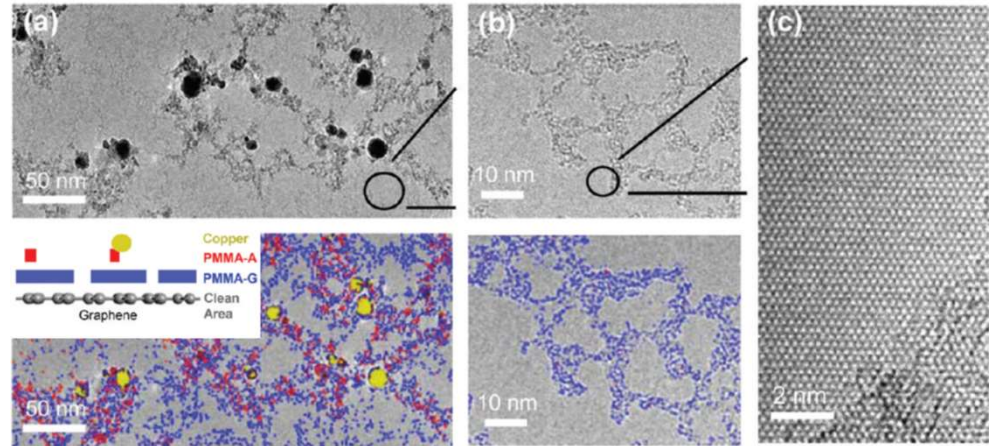
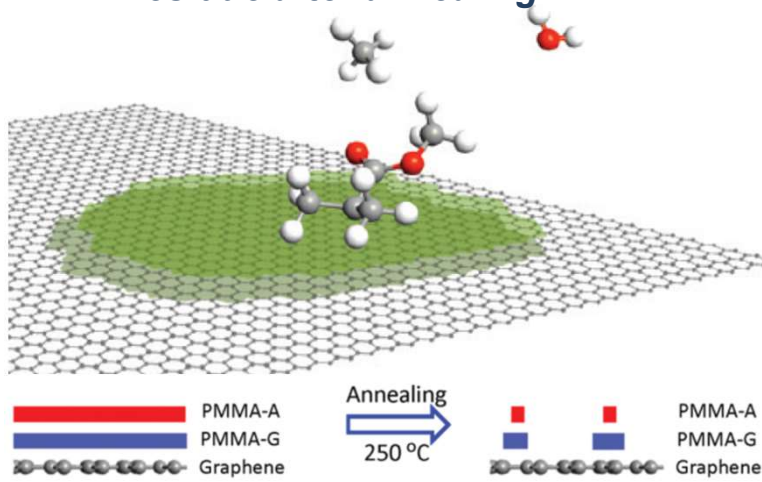


Delamination process of a ML MoS₂ film

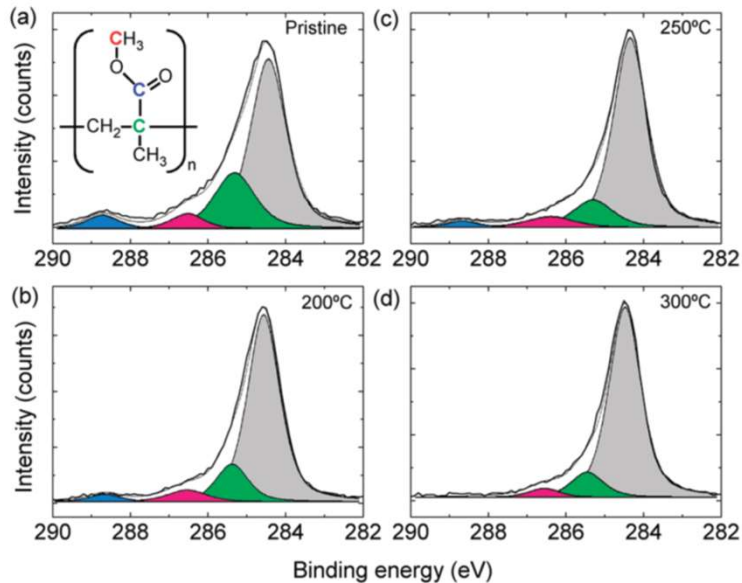


Residue Issue in Transfer

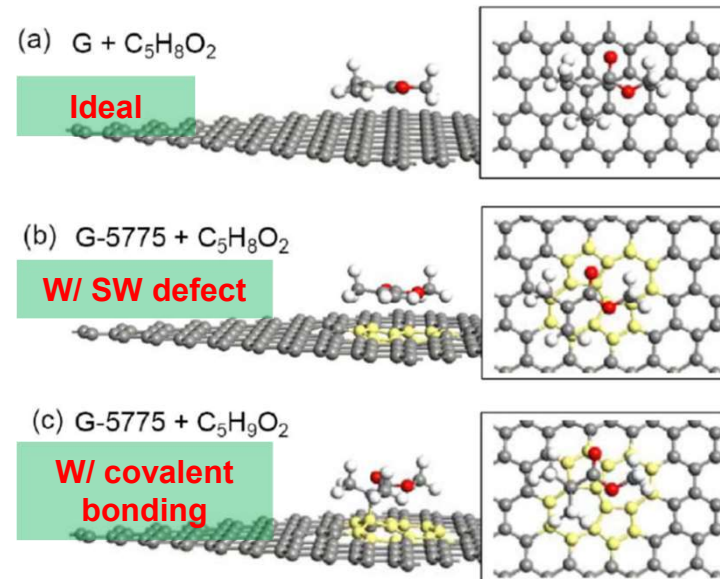
PMMA residue after annealing



XPS spectra of PMMA-transferred CVD graphene



Side and top view of the optimized adsorption of MMA



YC Lin et al. Nano Lett. (2011)